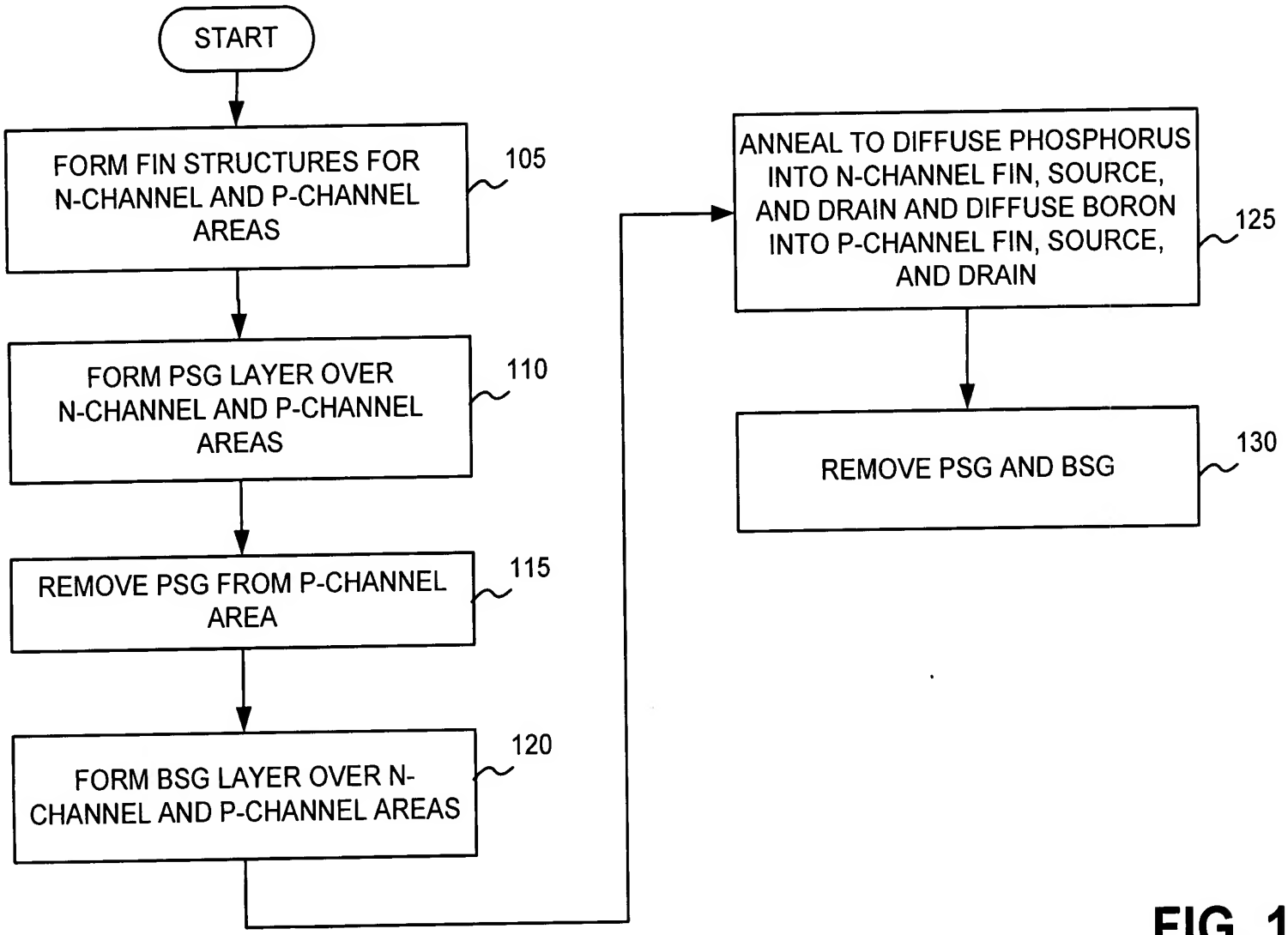
START
FORM FIN STRUCTURES FOR N-CHANNEL AND P-CHANNEL AREAS
105
FORM PSG LAYER OVER N-CHANNEL AND P-CHANNEL AREAS
110
REMOVE PSG FROM P-CHANNEL AREA
115
FORM BSG LAYER OVER N-CHANNEL AND P-CHANNEL AREAS
120
ANNEAL TO DIFFUSE PHOSPHORUS INTO N-CHANNEL FIN, SOURCE, AND DRAIN AND DIFFUSE BORON INTO P-CHANNEL FIN, SOURCE, AND DRAIN
125
REMOVE PSG AND BSG
130

FIG. 1

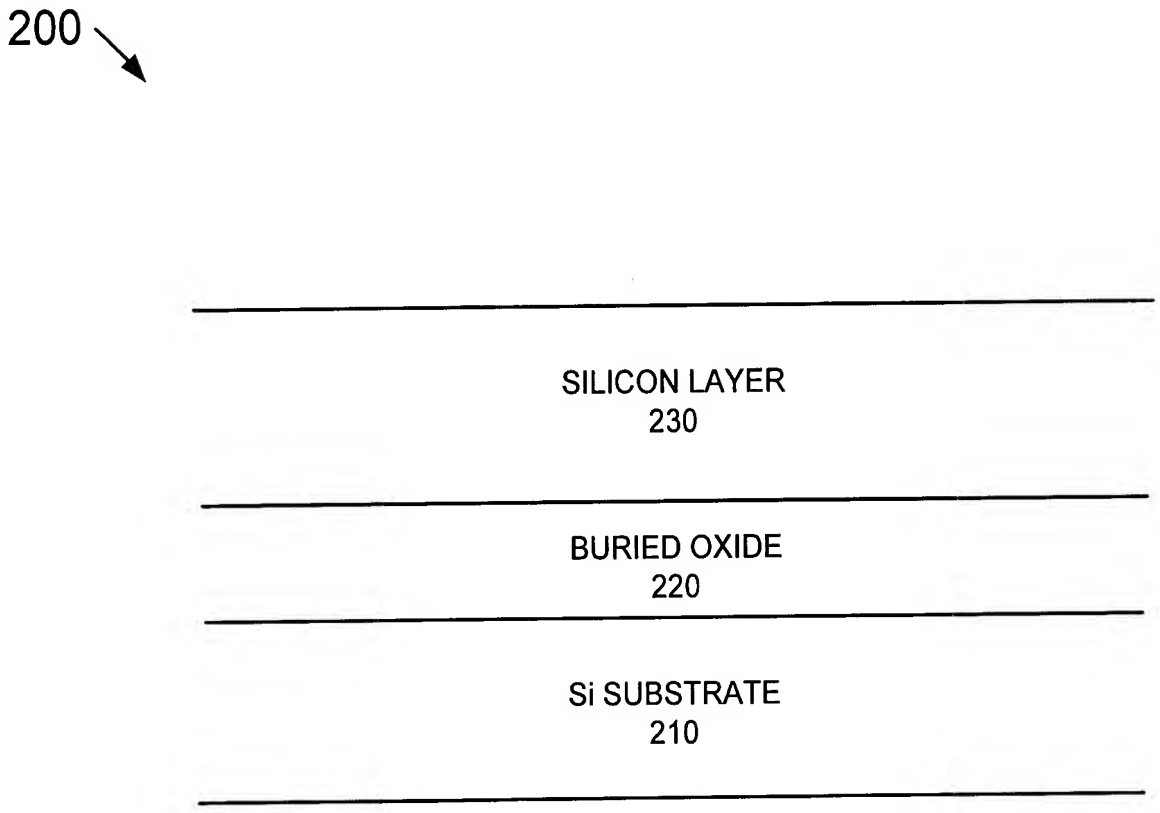

FIG. 2

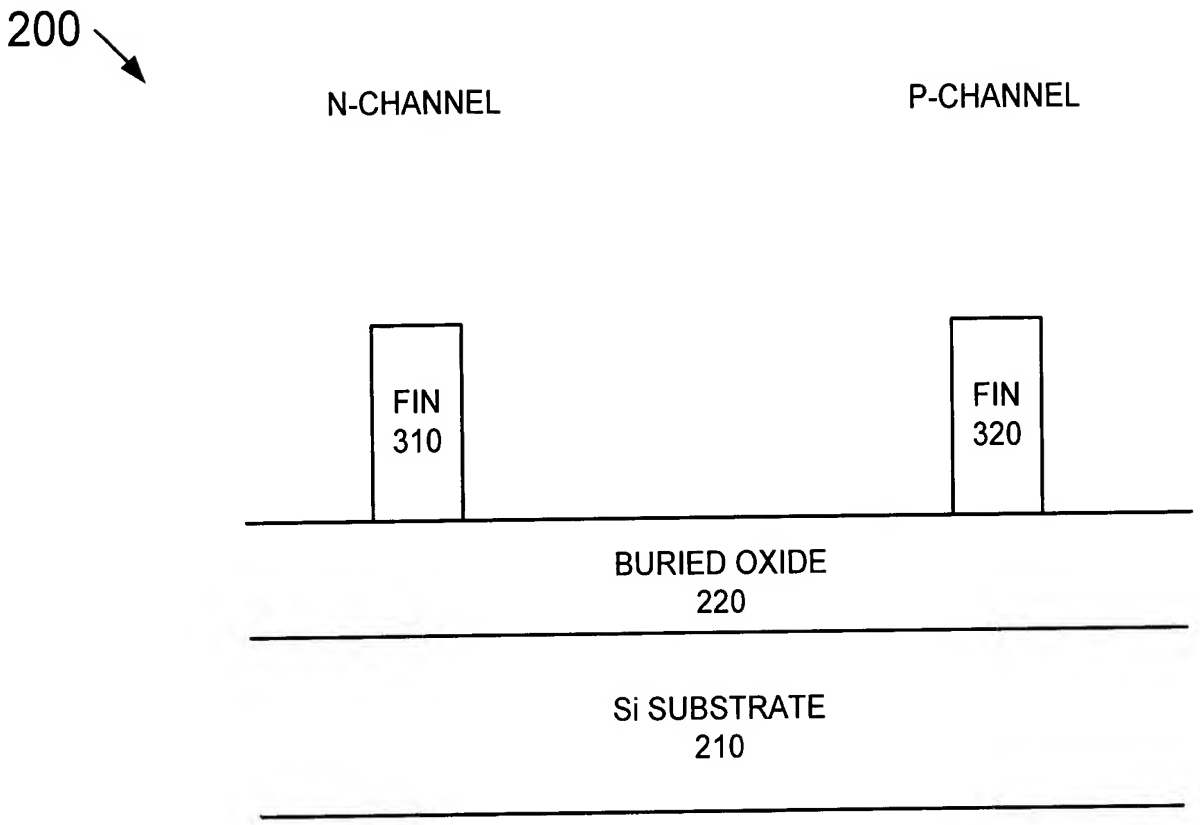
200
N-CHANNEL
P-CHANNEL
FIN
310
FIN
320
BURIED OXIDE
220
Si SUBSTRATE
210

FIG. 3A

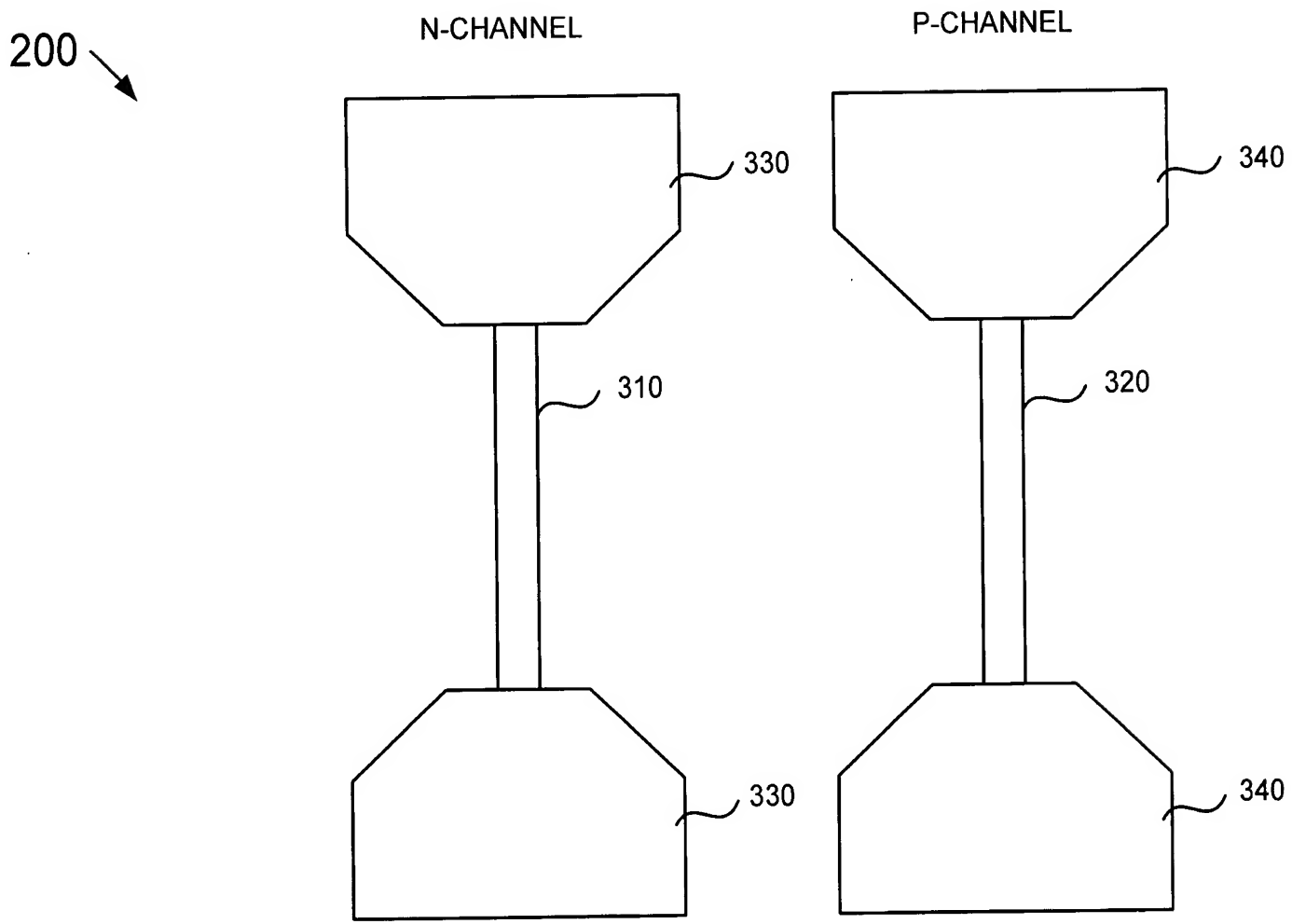

FIG. 3B

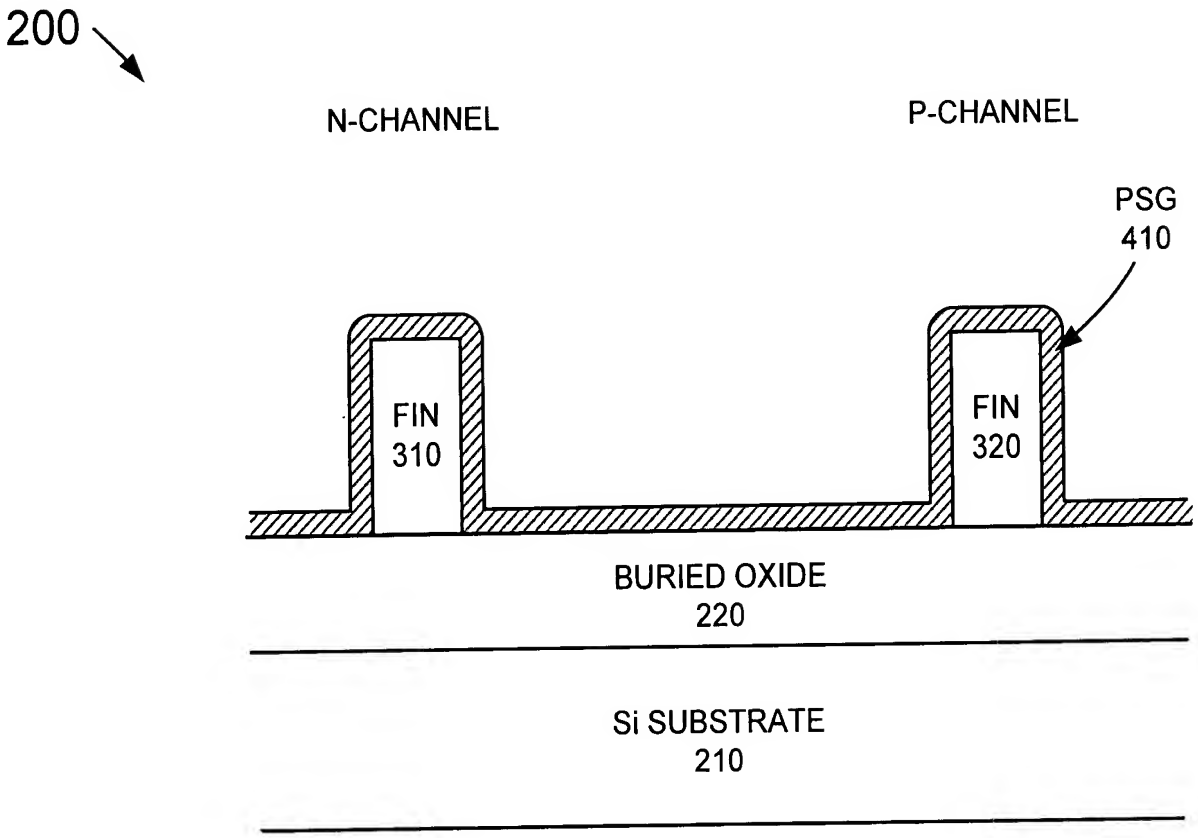
200
N-CHANNEL
P-CHANNEL
PSG
410
FIN
310
FIN
320
BURIED OXIDE
220
Si SUBSTRATE
210

FIG. 4

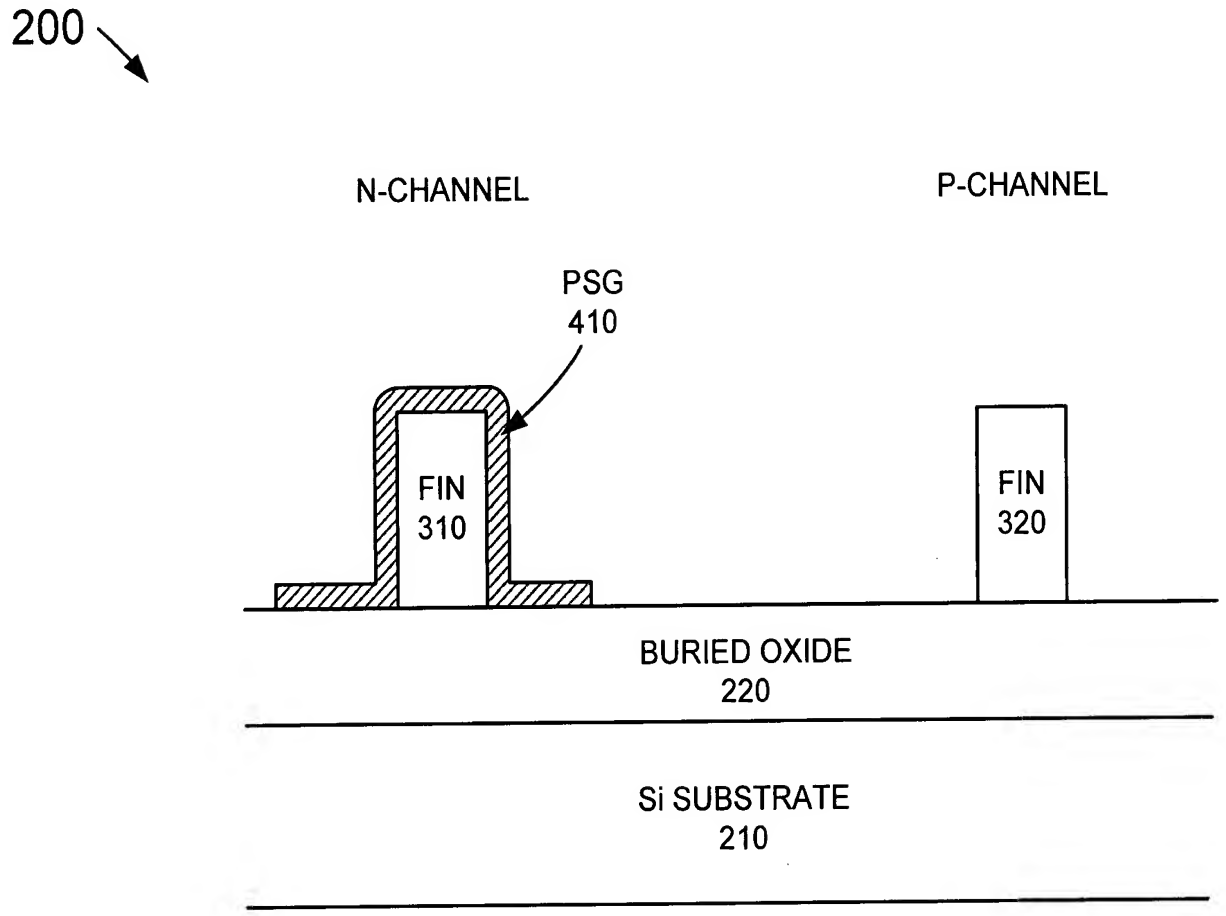
200
N-CHANNEL
P-CHANNEL
PSG
410
FIN
310
FIN
320
BURIED OXIDE
220
Si SUBSTRATE
210

FIG. 5

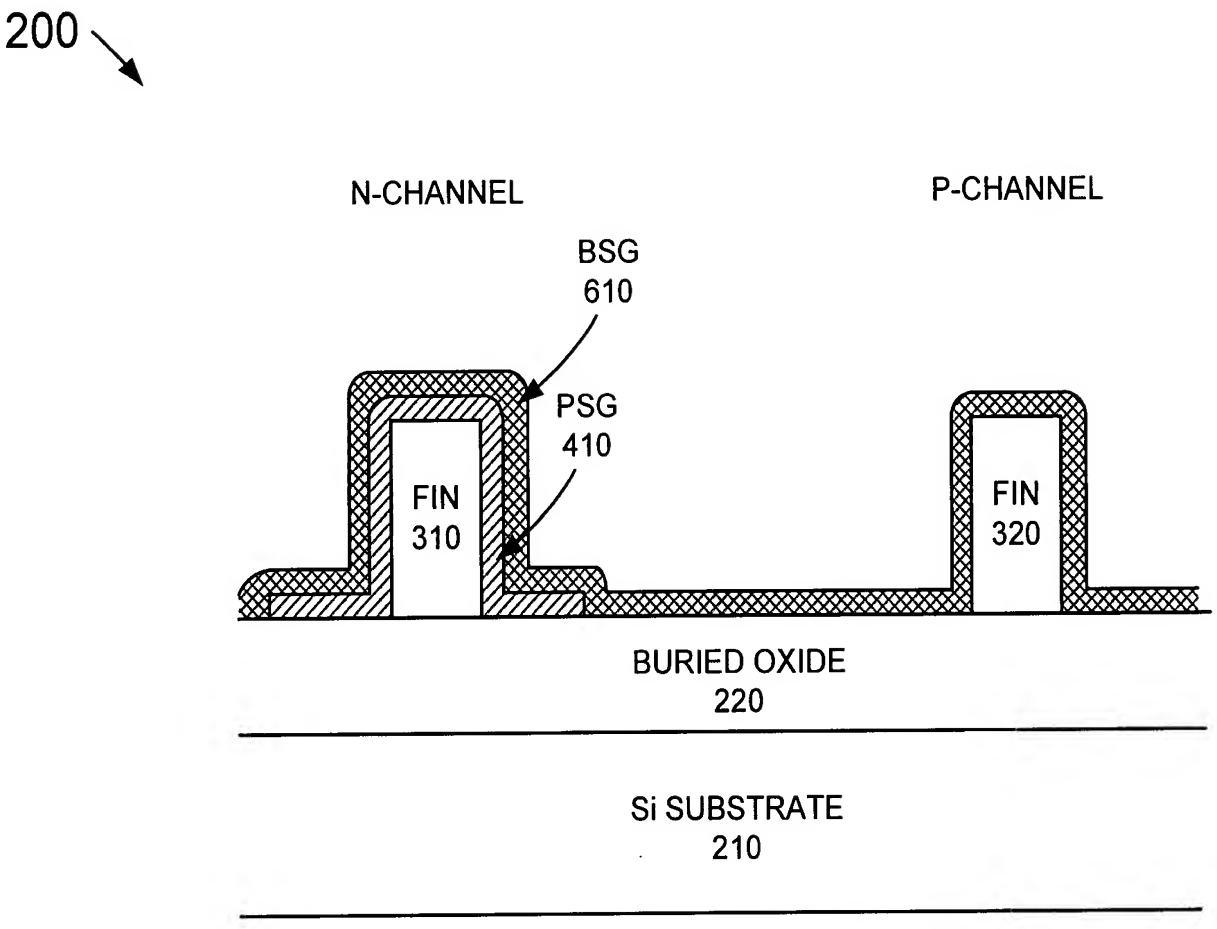
200
N-CHANNEL
P-CHANNEL
BSG
610
PSG
410
FIN
310
FIN
320
BURIED OXIDE
220
Si SUBSTRATE
210

FIG. 6

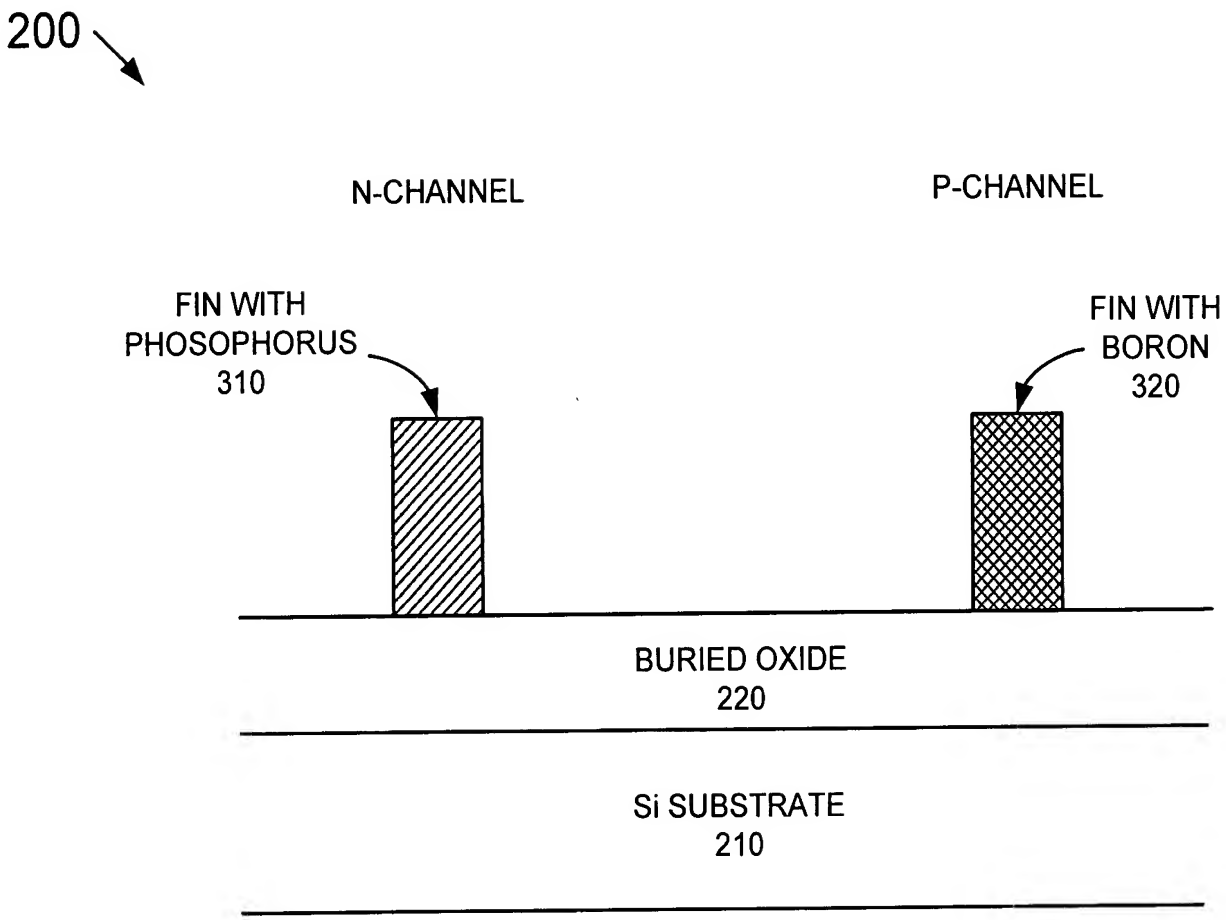
200
N-CHANNEL
P-CHANNEL
FIN WITH
PHOSOPHORUS
310
FIN WITH
BORON
320
BURIED OXIDE
220
Si SUBSTRATE
210

FIG. 7A

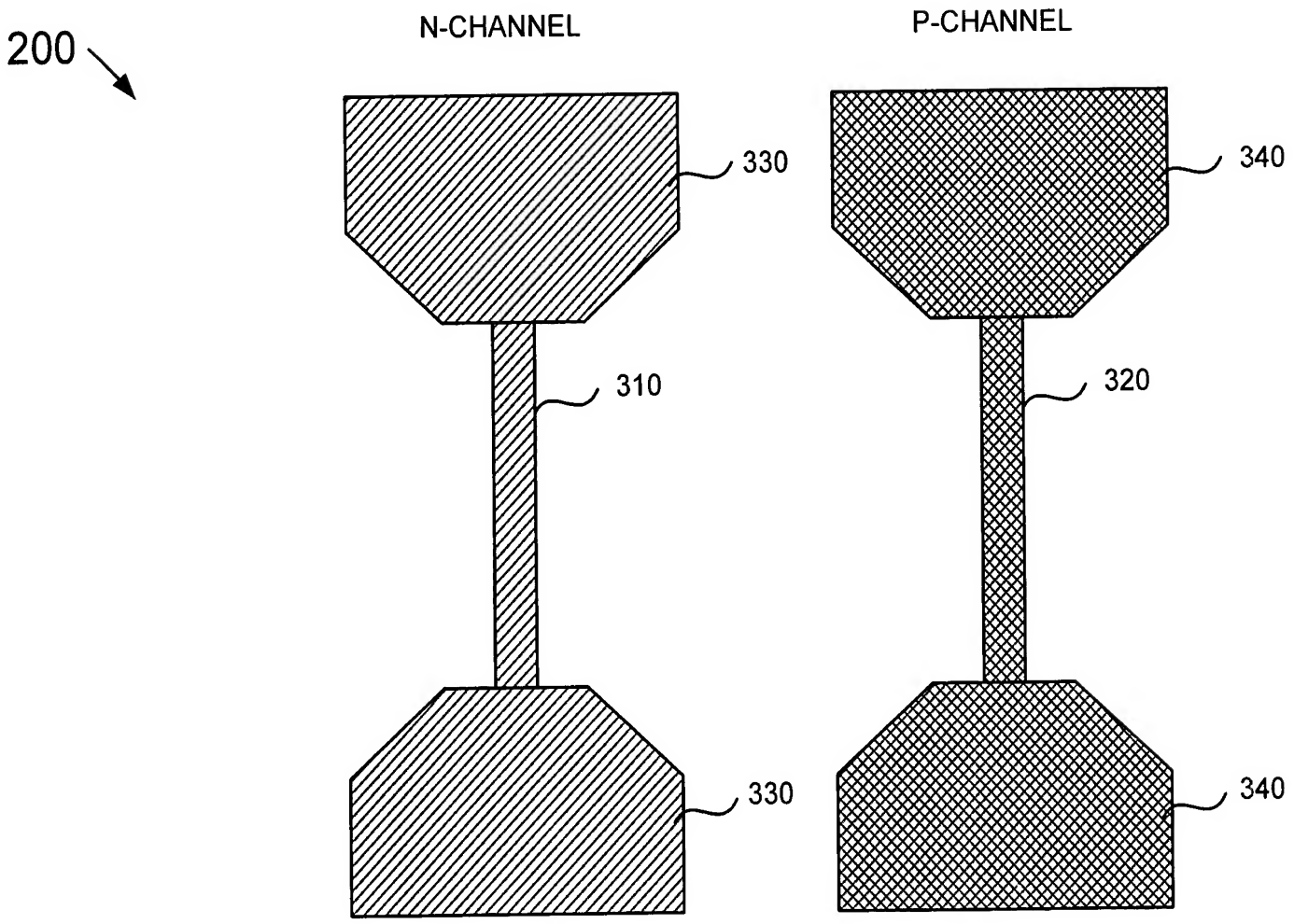

FIG. 7B

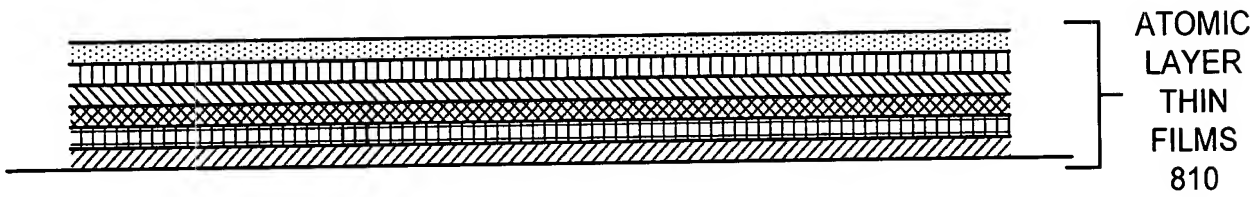

FIG. 8